



100V N-Channel MOSFET

Voltage

100 V

Current

9 A

Features

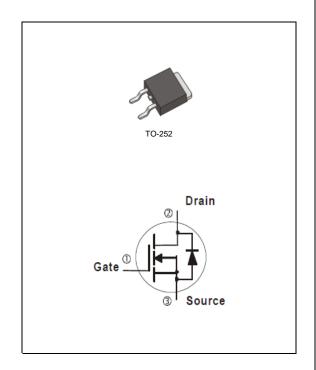
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@4.5A<152m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@3.0A<158m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)



• Case: TO-252 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMET	TER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	I _D	9	А	
	T _C =100°C		6		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	18		
Power Dissipation	T _C =25°C	Po	31	W	
	T _C =100°C		12		
Continuous Drain Current	T _A =25°C	I _D	2.4	А	
	T _A =70°C		1.9	А	
Power Dissipation	T _A =25°C		2.0		
Power Dissipation	T _A =70°C	Pb	1.3	W	
Single Pulse Avalanche Energy (Note 6)		E _{AS}	1.8	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	4.0	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_D =250uA	100	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.72	2.5	V		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =4.5A	-	130	152	mΩ		
		V _{GS} =4.5V,I _D =3A	-	135	158			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V,V _{GS} =0V	-	-	1	uA		
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 4)								
Total Gate Charge	Q_g	V _{DS} =60V, I _D =9A, V _{GS} =10V ^(Note 2,3)	_	19	-	nC		
Gate-Source Charge	Q_gs		-	2.9	-			
Gate-Drain Charge	Q_{gd}		-	3.2	-			
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	-	1021	-	pF		
Output Capacitance	Coss		_	38	-			
Reverse Transfer Capacitance	Crss	I=1.0IVII IZ	-	17	-			
Turn-On Delay Time	td _(on)	V 50V DI 5 60	-	6.1	-			
Turn-On Rise Time	t _r	V_{DS} =50V,RL=5.6 Ω , V_{GS} =10V, R _G =6 Ω (Note 2,3)	-	27	-	ns		
Turn-Off Delay Time	td _(off)		-	28	-			
Turn-Off Fall Time	t _f		-	11	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	,				9	Α		
Diode Forward Current	I _S				9	^		
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.74	1.2	V		

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ=25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =6A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing





TYPICAL CHARACTERISTIC CURVES

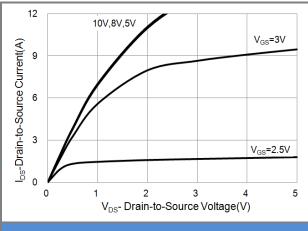


Fig.1 On-Region Characteristics

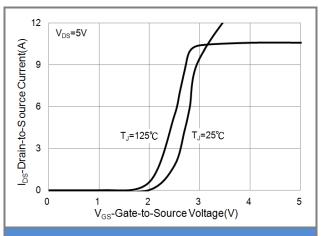


Fig.2 Transfer Characteristics

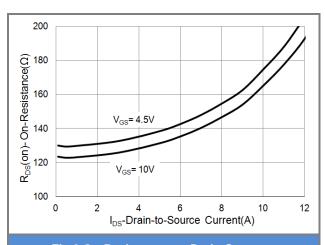


Fig.3 On-Resistance vs. Drain Current

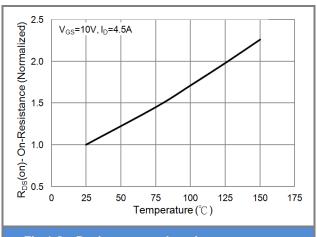


Fig.4 On-Resistance vs. Junction temperature

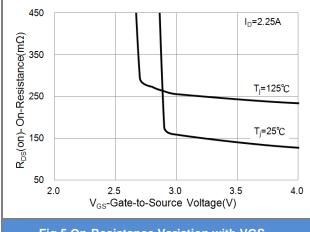


Fig.5 On-Resistance Variation with VGS.

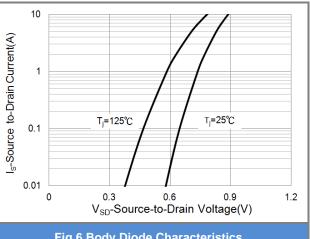


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

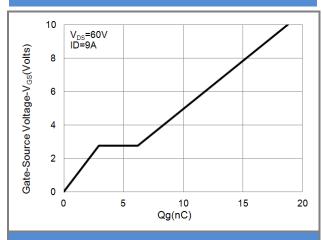


Fig.7 Gate-Charge Characteristics

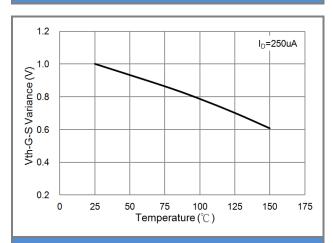


Fig.9 Threshold Voltage Variation with Temperature.

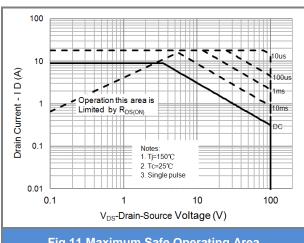


Fig.11 Maximum Safe Operating Area

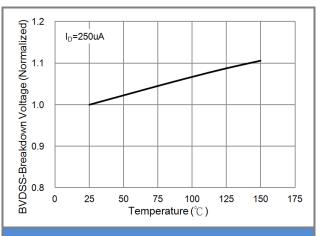


Fig.8 Breakdown Voltage Variation vs. Temperature

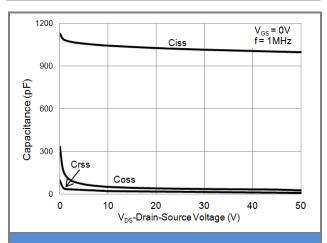


Fig.10 Capacitance vs. Drain-Source Voltage.





TYPICAL CHARACTERISTIC CURVES

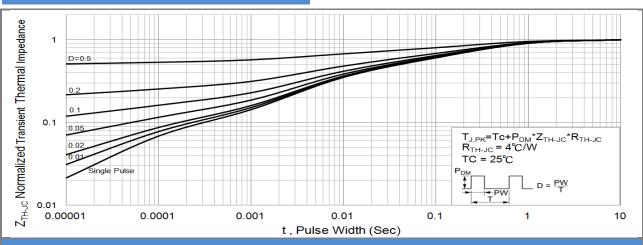
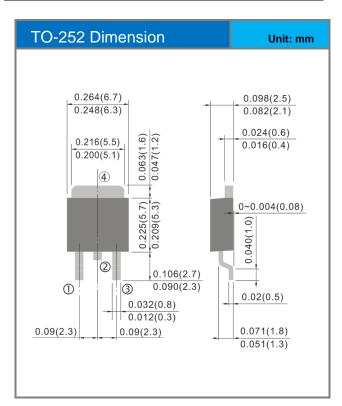


Fig.12 Normalized Thermal Transient Impedance





Packaging Information



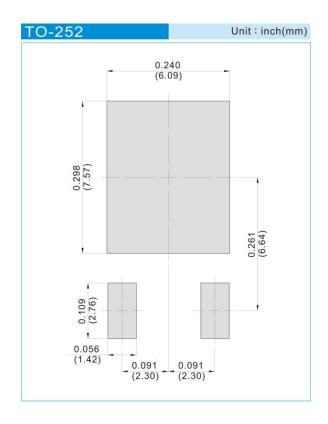




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version	
PJD9N10A_L2_00001	TO-252	3,000pcs / 13" reel	D9N10A	Halogen free	

MOUNTING PAD LAYOUT







Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are
 responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no
 representation or warranty that such applications will be suitable for the specified use without further testing or
 modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.